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(54) **SEMICONDUCTOR DEVICE AND METHOD  
FOR FORMING A SRAM MEMORY CELL  
STRUCTURE**

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(71) Applicant: **Taiwan Semiconductor  
Manufacturing Company, Ltd.,  
Hsinchu (TW)**

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(72) Inventors: **Hidehiro FUJIWARA**, Hsinchu (TW);  
**Yi-Hsin NIEN**, Hsinchu (TW);  
**Hung-Jen LIAO**, Hsinchu (TW)

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(73) Assignee: **Taiwan Semiconductor  
Manufacturing Company, Ltd.,  
Hsinchu (TW)**

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(57) **ABSTRACT**

An apparatus includes memory cells. A first memory cell of the memory cells includes a first write port laid out in a first doping region and a first read port laid out in a second doping region. The first read port is separated from the first write port by a second write port of a second memory cell of the memory cells.

